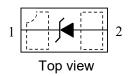


Ultra Small ESD Protector

Description

The PESDXC2FD5VU ESD protector is designed to replace multilayer varistors(MLVs) in portable applications such as cell phones, notebook computers, and PDA's. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs. The PESDXC2FD5VU protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. The PESDXC2FD5VU is available in a DFN1006-2L package with working voltages of 5 volt. It gives designer the flexibility to protect one unidirectional line in applications where arrays are not practical. Additionally, it may be "sprinkled" around the board in applications where board space is at a premium.



Feature

- Ultra low capacitance 0.5pF
- DFN1006-2L package
- Replacement for MLV(0402)
- Unidirectional configurations
- Response time is typically < 1 ns</p>
- Protect one I/O or power line
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) ±25KV (air), ±20KV (contact); IEC 61000-4-4 (EFT) 40A (5/50ns)

Applications

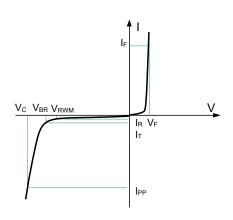
- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP3 players

Mechanical Characteristics

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- ➤ Qualified max reflow temperature:260°C
- Device meets MSL 1 requirements
- ➤ Pure tin plating: 7 ~ 17 um
- Pin flatness:≤3mil

Electronics Parameter

Symbol	Parameter
V_{RWM}	Peak Reverse Working Voltage
I _R	Reverse Leakage Current @ V _{RWM}
V_{BR}	Breakdown Voltage @ I⊤
I _T	Test Current
I _{PP}	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ I _{PP}
P _{PP}	Peak Pulse Power
CJ	Junction Capacitance
I _F	Forward Current
V _F	Forward Voltage @ I _F



Electrical characteristics per line@25℃(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}				5.0	V
Breakdown Voltage	V _{BR}	I _t =1mA	5.4	7.0	8.5	V
Reverse Leakage Current	I _R	V _{RWM} =5V			1.0	μA
Forward Voltage	V _F	I _F =10mA		0.8	1.25	V
Clamping Voltage	Vc	I_{PP} =1A $t_P = 8/20 \mu S$		8.5	9.2	V
Clamping Voltage	Vc	I_{PP} =6.5A t_P = 8/20 μ S		14.0	16.0	V
Junction Capacitance	C _j	V _R =0V f = 1MHz		0.5	0.65	pF

Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power (t _p =8/20µs)	P _{pp}	100	W
Lead Soldering Temperature	T∟	260(10 sec)	${\mathbb C}$
Operating Temperature	TJ	-55 to 125	${\mathbb C}$
Storage Temperature	T _{STG}	-55 to 150	$^{\circ}$

Typical Characteristics

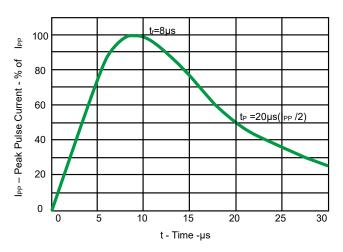


Fig 1.Pulse Waveform

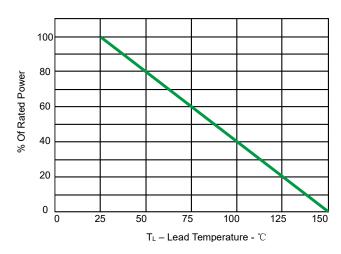


Fig 2.Power Derating Curve

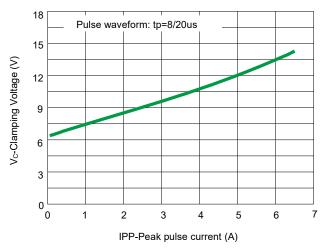


Fig 3. Clamping voltage vs. Peak pulse current

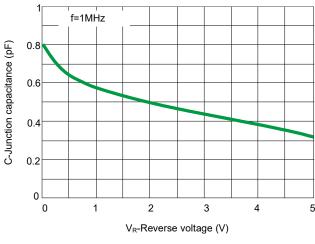
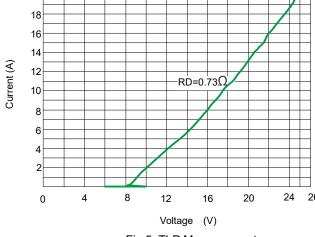


Fig 4. Capacitance vs. Reveres voltage



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Fig 5. TLP Measurement

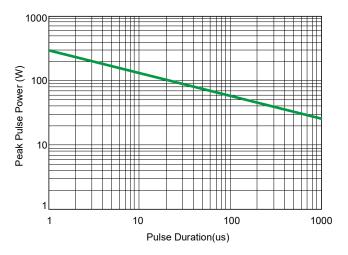
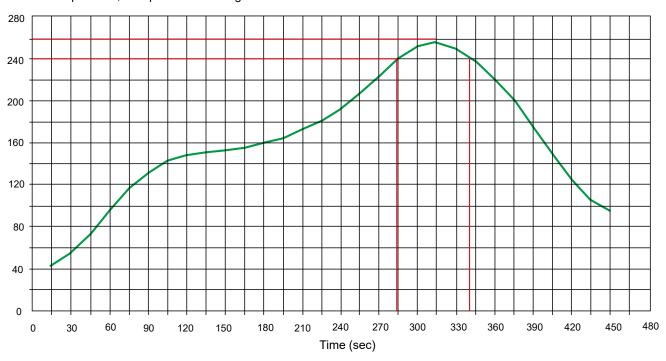


Fig 6. Non Repetitive Peak Pulse Power vs. Pulse time

Solder Reflow Recommendation

Peak Temp=257°C, Ramp Rate=0.802deg. °C/sec

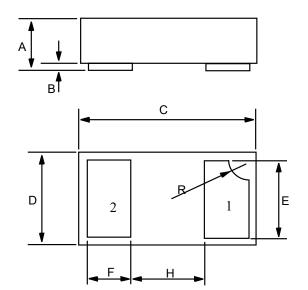


PCB Design

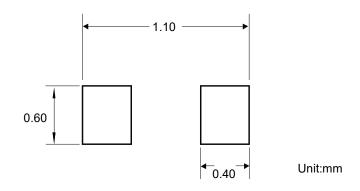
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- Keep the length of via holes in mind! The longer the more inductance they will have.

Product dimension (DFN1006-2L)

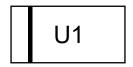


D:	Inches		Millimeters		
Dim	MIN	MAX	MIN	MAX	
Α	0.013	0.020	0.34	0.50	
В	0.000	0.002	0.00	0.05	
С	0.037	0.043	0.95	1.080	
D	0.022	0.027	0.55	0.680	
Е	0.016	0.024	0.40	0.60	
F	0.008	0.012	0.20	0.30	
Н	0.015Typ.		0.40Typ.		
R	0.001	0.005	0.05	0.15	



Suggested PCB Layout

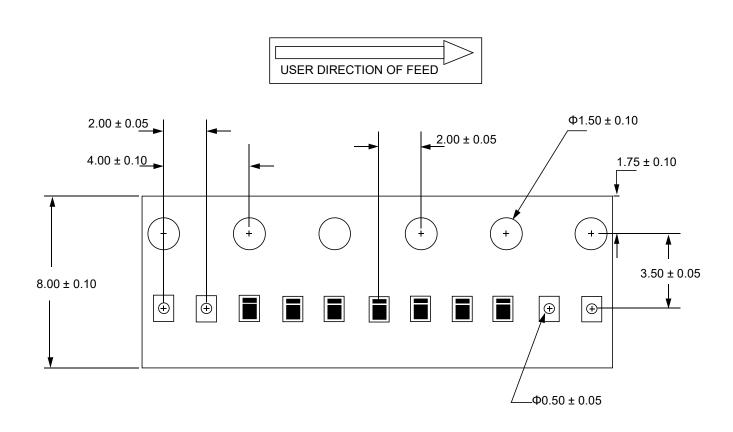
Marking information



Ordering information

Device	Device Package		Shipping
PESDXC2FD5VU	DFN1006-2L (Pb-Free)	7"	10000 / Tape & Reel

Load with information



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